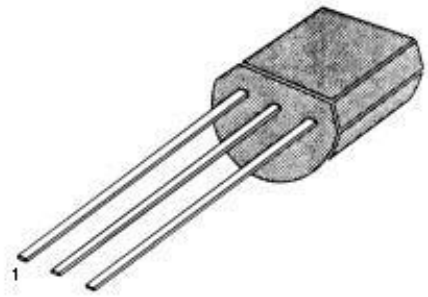
A1266
PNP Epitaxial Silicon Transistor

TO-92



1. Emitter 2. Collector 3. Base

Features

- Collector-Emitter Voltage: V_{CEO}=-50V
- Collector Dissipation: P_C(max)=625mW

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Characteristics (TA=25°C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -100μA, I_E=0	-50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -0.1mA, I_B=0	-50		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -100μA, I_C=0	-5		V
Collector Cut-off Current	I_{CBO}	V_{CB}= -50V, I_E=0		-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}= -5V, I_C=0		-0.1	μA
DC Current Gain	h_{FE1}	V_{CE}= -6V, I_C= -2mA	70	400	
	h_{FE2}	V_{CE}= -6V, I_C= -150mA	25		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C= -100mA, I_B= -10mA		-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C= -100mA, I_B= -10mA		-0.1	V
Transition Frequency	f_T	V_{CE}= -10V, I_C= -1mA			
		f=30MHz	80		MHz

h_{FE}(1) CLASSIFICATION

Classification	O	Y	GR
h_{FE}(1)	70 – 140	120 – 300	300 – 400

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